

2N3467
2N3468

SILICON
PNP TRANSISTORS



TO-39 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3467 and 2N3468 are silicon PNP switching transistors designed for core driver applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Power Dissipation ($T_C=25^\circ\text{C}$)
Operating and Storage Junction Temperature
Thermal Resistance
Thermal Resistance

SYMBOL	2N3467	2N3468	UNITS
V_{CBO}	40	50	V
V_{CEO}	40	50	V
V_{EBO}		5.0	V
I_C		1.0	A
P_D		1.0	W
P_D		5.0	W
T_J, T_{stg}		-65 to +200	$^\circ\text{C}$
Θ_{JA}		175	$^\circ\text{C/W}$
Θ_{JC}		35	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3467		2N3468		UNITS
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=30\text{V}$	-	100	-	100	nA
I_{CBO}	$V_{CB}=30\text{V}, T_A=100^\circ\text{C}$	-	15	-	15	μA
I_{CEV}	$V_{CE}=30\text{V}, V_{BE}=3.0\text{V}$	-	100	-	100	nA
I_{BEV}	$V_{CE}=30\text{V}, V_{BE}=3.0\text{V}$	-	120	-	120	nA
BV_{CBO}	$I_C=10\mu\text{A}$	40	-	50	-	V
BV_{CEO}	$I_C=10\text{mA}$	40	-	50	-	V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0	-	5.0	-	V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.3	-	0.36	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	0.5	-	0.6	V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$	-	1.0	-	1.2	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	1.0	-	1.0	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	0.8	1.2	0.8	1.2	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$	-	1.6	-	1.6	V
h_{FE}	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	40	-	25	-	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	40	120	25	75	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$	40	-	20	-	

R2 (26-July 2013)

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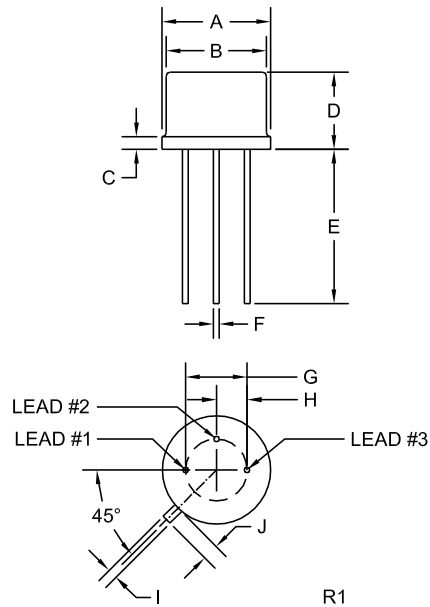
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3467		2N3468		UNITS
		MIN	MAX	MIN	MAX	
f_T	$V_{CE}=10\text{V}$, $I_C=50\text{mA}$, $f=100\text{MHz}$	175	-	150	-	MHz
C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=100\text{kHz}$	-	25	-	25	pF
C_{ib}	$V_{EB}=0.5\text{V}$, $I_C=0$, $f=100\text{kHz}$	-	100	-	100	pF
t_{on}	$V_{CC}=30\text{V}$, $V_{BE}=2.0\text{V}$, $I_C=500\text{mA}$, $I_{B1}=50\text{mA}$	-	40	-	40	ns
t_{off}	$V_{CC}=30\text{V}$, $I_C=500\text{mA}$, $I_{B1}=I_{B2}=50\text{mA}$	-	90	-	90	ns
Q_T	$V_{CC}=30\text{V}$, $I_C=500\text{mA}$, $I_B=50\text{mA}$	-	6.0	-	6.0	nC

TO-39 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

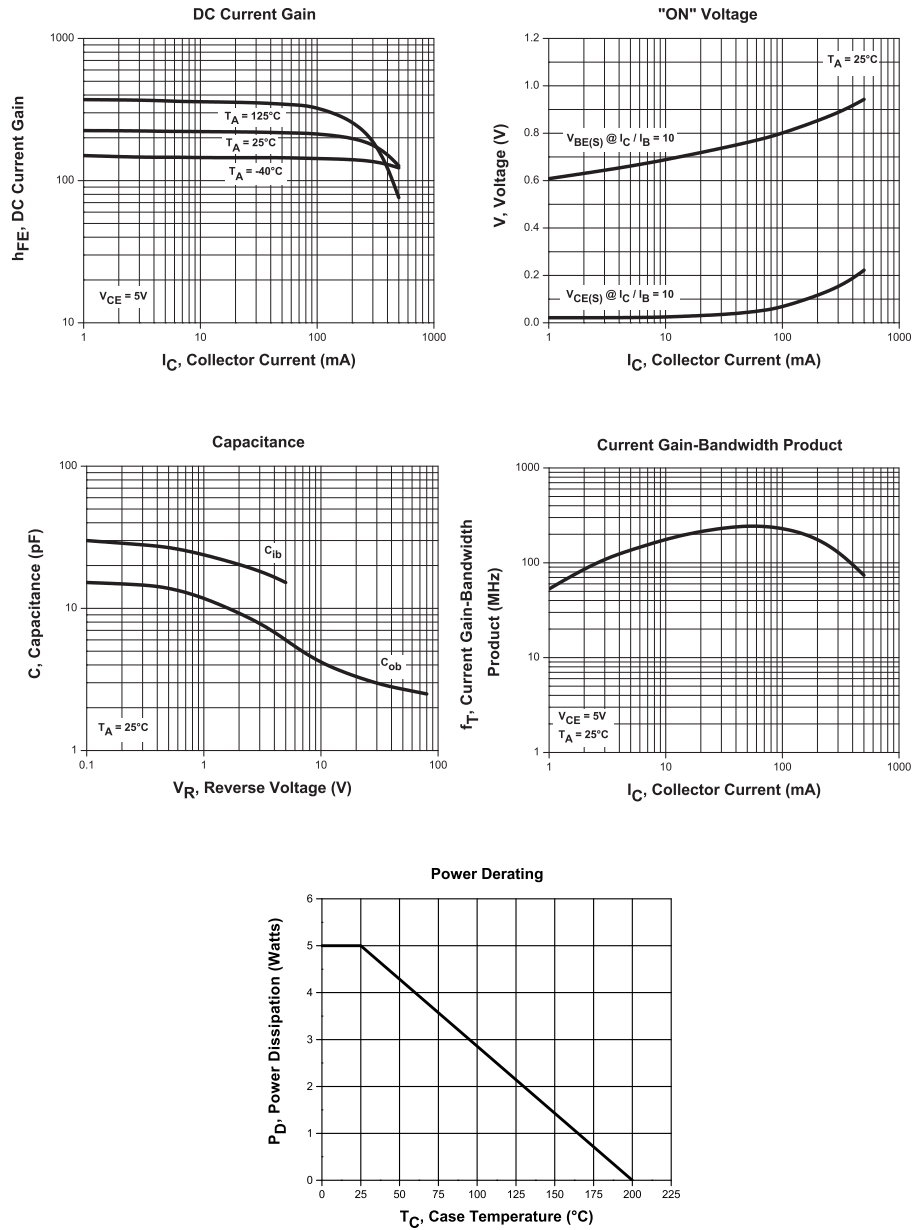
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TYPICAL ELECTRICAL CHARACTERISTICS



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AMEYA360

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